

4-Unit 400mA Transistor Array

IR2C26

T-43-25

IR2C26 4-Unit 400mA Transistor Array

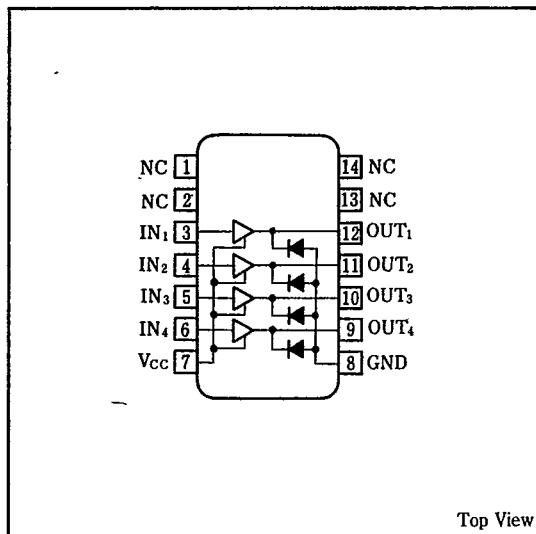
■ Description

The IR2C26 is a 4-circuit-driver IC, which consists of an input inverter and a current source type output section. The output section is composed of a PNP transistor and an NPN Darlington transistor, with the base current of the PNP transistor constant. A clamp diode is placed between each output and GND; V_{CC} and GND are common for the 4 circuits. This transistor array is suitable for driving replays, printers, LED fluorescent display tubes and lamps as well as for interface with logic systems of the MOS or bipolar transistor, solenoids and small motors.

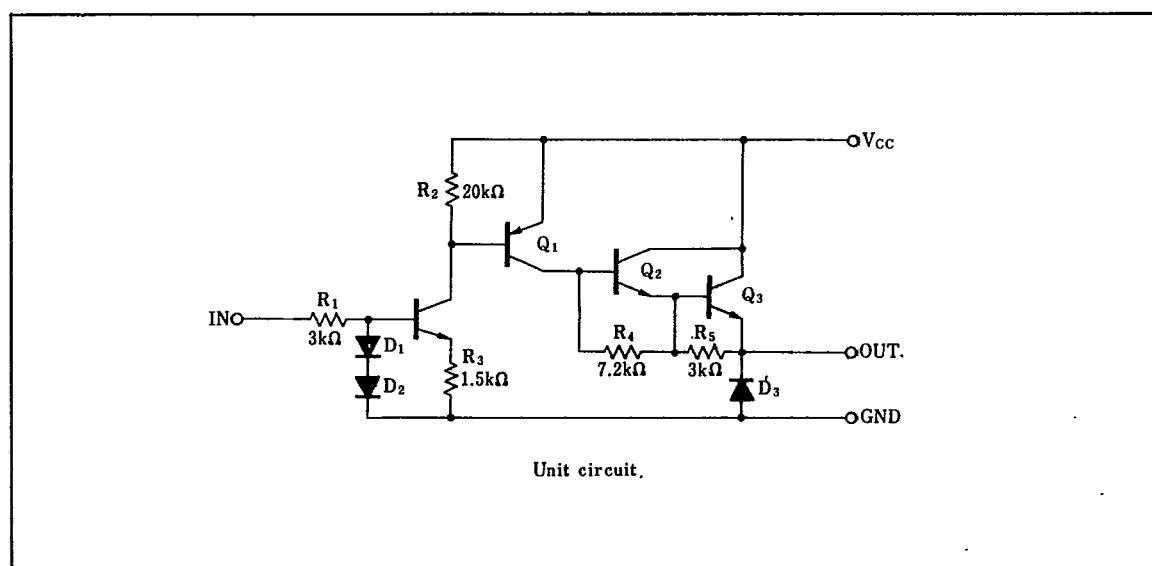
■ Features

1. High output current, I_{OUT}= -400mA (MAX.)
2. High output breakdown voltage BV_{CEO}=45V (MAX.)
3. Built-in output clamp diode
4. Darlington structure, output current source type
5. 14-pin dual-in-line package

■ Pin Connections



■ Equivalent Circuit



SHARP

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Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V _{CC}		45	V
Voltage between collector and emitter	V _{CBO}	When output is "L"	45	V
Output current	I _{OUT}	Current per circuit at the time of output being "H"	-400	mA
Input voltage	V _{IN}		0~10	V
Clamp diode reverse voltage	V _R		45	V
Clamp diode forward current	I _F		-400	mA
Power dissipation	P _D	T _a ≤25°C	970	mW
P _D derating ratio	ΔP _D /°C	T _a >25°C	7.76	mW/°C
Operating temperature	T _{opr}		-20~+75	°C
Storage temperature	T _{stg}		-55~+150	°C

**Recommended Operating Conditions**

(Unless otherwise specified, Ta=-20~+75°C)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{CC}				45	V
Output current (per circuit)	I _{OUT}	at 15% duty			-350	mA
		at 65% duty			-100	mA
Input "High" voltage	V _H	I _{OUT} =-350mA	2.4			V
Input "Low" voltage	V _L				0.2	V

Electrical Characteristics

(Unless otherwise specified, Ta=-20~+75°C)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Power leakage current	I _{CC(Leak)}	V _{CC} =45V, V _{IN} =0.2			100	μA
Saturation voltage between collector and emitter	V _{CBO(sat)}	V _{CC} =10V, V _{IN} =2.4V, I _{OUT} =-350mA			2.4	V
		V _{CC} =10V, V _{IN} =2.4V, I _{OUT} =-100mA			2	V
Input current	I _{IN}	V _{CC} =10V, V _{IN} =3V			1.2	mA
		V _{CC} =10V, V _{IN} =10V			5	mA
Supply current at ON	I _{CC}	V _{CC} =45V, V _{IN} =3V			5	mA
Clamp diode forward voltage	V _F	I _F =-350mA			-2.4	V
Clamp diode reverse voltage	V _R	I _R =100 μA	45			V

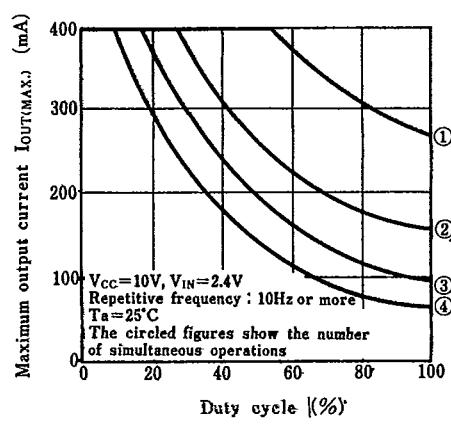
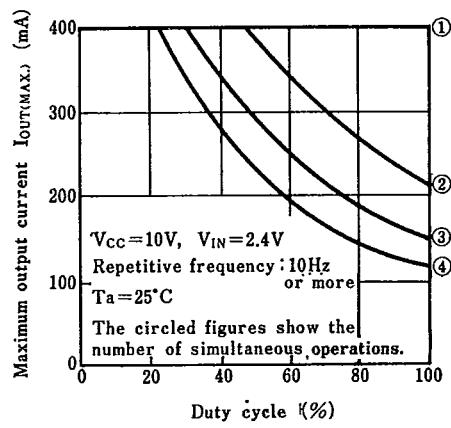
Electrical Characteristic Curves (Unless otherwise specified, Ta=+25°C)

Maximum output current—Duty cycle

Maximum output current—Duty cycle

Characteristics (1)

Characteristics (2)



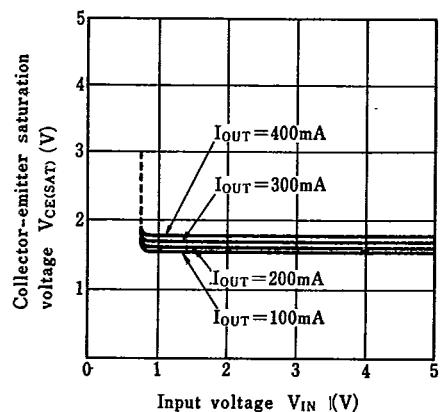
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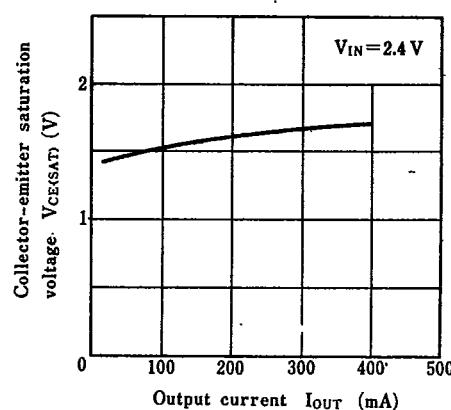
Collector-emitter saturation voltage

—Input voltage Characteristics



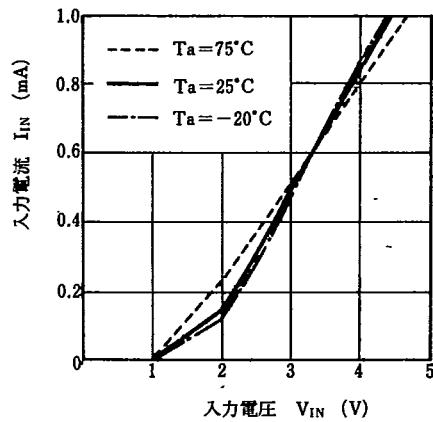
Collector-emitter saturation voltage

—Output current Characteristics



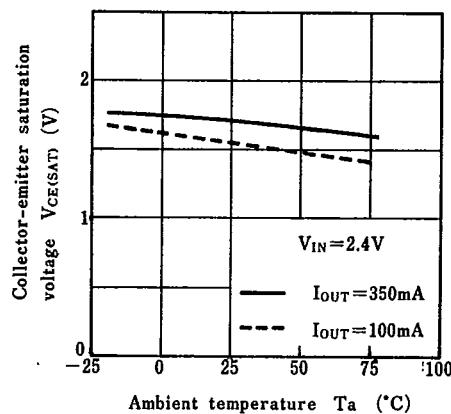
Input current—Input voltage

Characteristics



Collector-emitter saturation voltage

—Ambient temperature Characteristics



Input current—Ambient temperature

Characteristics

